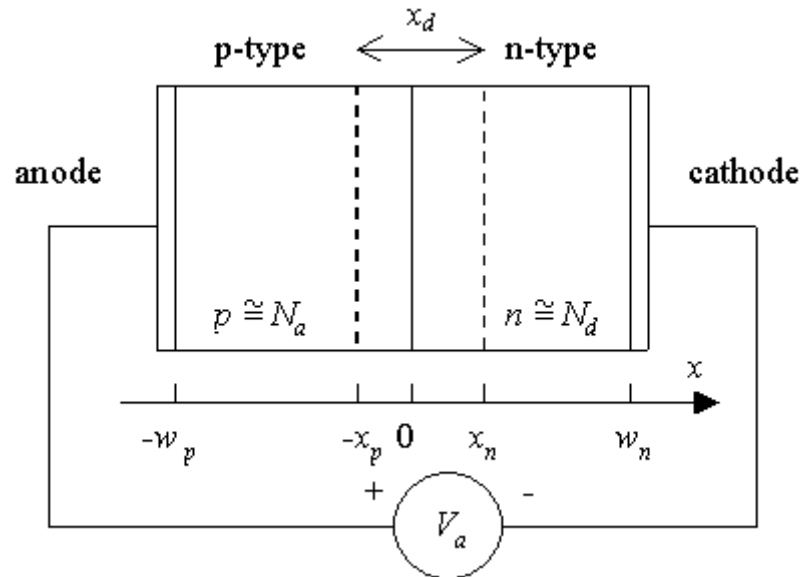


# PN Junction Supplements

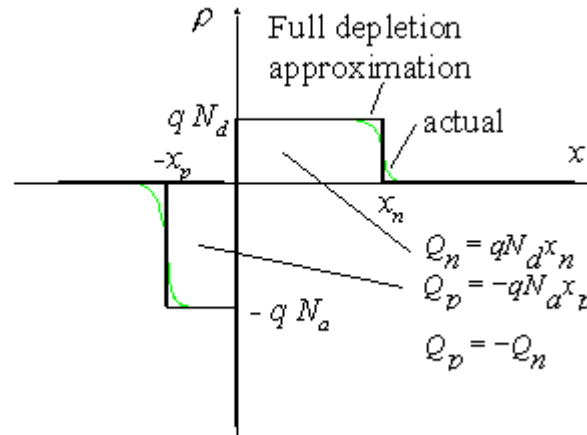
Deog-Kyoon Jeong

# Cross Section of a PN Junction



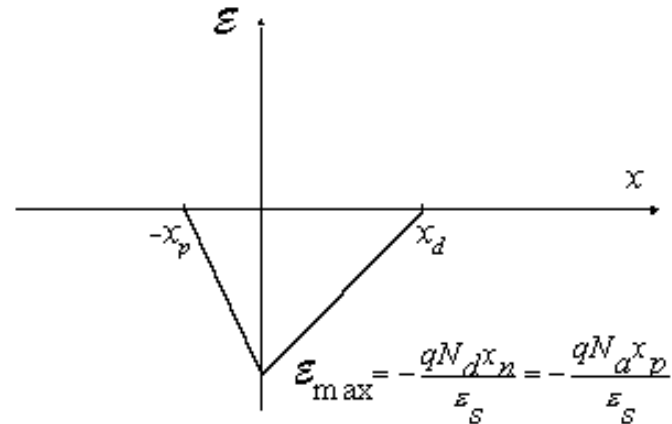
- **Assumptions**
  - The doped regions are uniformly doped.
  - The transition between the two regions is abrupt.

# Charge Density Profile



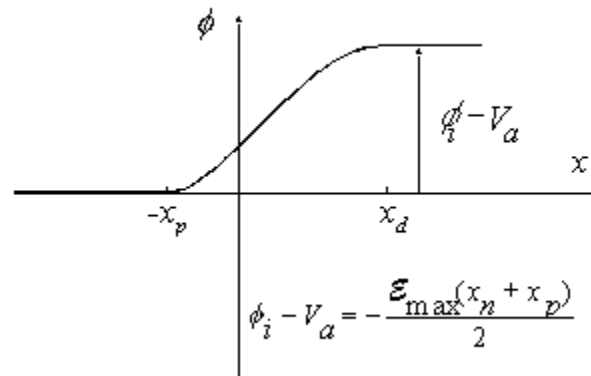
- $\rho = q(p - n + N_d^+ + N_a^-) \approx q(N_d^+ + N_a^-)$
- $\rho(x) = 0$  ( $x < -x_p$  or  $x > x_n$ )
- $\rho(x) = -qN_a$  ( $-x_p < x < 0$ )
- $\rho(x) = +qN_d$  ( $0 < x < x_n$ )

# Electric Field



- $\frac{dE}{dx} = \frac{\rho(x)}{\epsilon_s}$  : Gauss's law
- $E(x) = 0$  ( $x < -x_p$  or  $x > x_n$ )
- $E(x) = -\frac{qN_a(x+x_p)}{\epsilon_s}$  ( $-x_p < x < 0$ )
- $E(x) = +\frac{qN_d(x-x_n)}{\epsilon_s}$  ( $0 < x < x_n$ )
- $N_a x_p = N_d x_n$

# Built In Potential



- $$\phi_1 - V_a = \frac{qN_d x_n^2}{2\epsilon_s} + \frac{qN_a x_p^2}{2\epsilon_s}$$

# Depletion Region Width

- $x_d = x_n + x_p$
- $N_a x_p = N_d x_n$
- $\phi_1 - V_a = \frac{qN_d x_n^2}{2\epsilon_s} + \frac{qN_a x_p^2}{2\epsilon_s}$
- $x_d = \sqrt{\frac{2\epsilon_s}{q} \left( \frac{1}{N_a} + \frac{1}{N_d} \right) (\phi_1 - V_a)}$
- $x_n = \sqrt{\frac{2\epsilon_s}{q} \frac{N_a}{N_d} \frac{1}{N_a + N_d} (\phi_1 - V_a)}$
- $x_p = \sqrt{\frac{2\epsilon_s}{q} \frac{N_d}{N_a} \frac{1}{N_a + N_d} (\phi_1 - V_a)}$

# Junction Capacitance

- $C(V_a) = \left| \frac{dQ(V_a)}{dV_a} \right|$
- $\rho(x) = +qN_d (0 < x < x_n)$
- $x_n = \sqrt{\frac{2\varepsilon_s N_a}{q N_d N_a + N_d} (\phi_1 - V_a)}$
- $C_j = \sqrt{\frac{q\varepsilon_s N_a N_d}{2(\phi_1 - V_a) N_a + N_d}} = \frac{\varepsilon_s}{x_d}$  : voltage dependent
- $C_{j0} = \sqrt{\frac{q\varepsilon_s N_a N_d}{2\phi_1 N_a + N_d}}$  : zero bias capacitance
- $C_j = \frac{C_{j0}}{\sqrt{1 - \frac{V_a}{\phi_1}}}$

# References

- **B. Van Zeghbroeck, 2011**  
([http://ecee.colorado.edu/~bart/book/book/chapter4/ch4\\_3.htm#4\\_3\\_3](http://ecee.colorado.edu/~bart/book/book/chapter4/ch4_3.htm#4_3_3))